

S/N 09/945,535



PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Kie Y. Ahn et al.	Examiner:	David S. Blum
Serial No.:	09/945,535	Group Art Unit:	2813
Filed:	August 30, 2001	Docket:	1303.026US1
Title:	HIGHLY RELIABLE AMORPHOUS HIGH-K GATE OXIDE ZrO ₂		

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

MS Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Supplemental Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. §1.97(c)(2), Applicants have included the fee of \$180.00 as set forth in 37 C.F.R. §1.17(p). Please charge any additional fees or credit any overpayment to Deposit Account No. 19-0743.

06/15/2005 AAD0F01 00000030 09945535

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The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

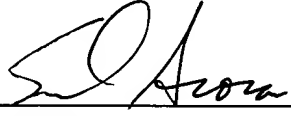
Pursuant to 37 C.F.R. 1.98(a)(2), Applicant believes that copies of cited U.S. Patents and Published Applications are no longer required to be provided to the Office. Notification of this change was provided in the United States Patent and Trademark Office OG Notices dated October 12, 2004. Thus, Applicant has not included copies of any US Patents or Published Applications cited with this submission. Should the Office require copies to be provided, Applicant respectfully requests that notice of such requirement be directed to Applicant's below-signed representative. Applicant acknowledges the requirement to submit copies of foreign patent documents and non-patent literature in accordance with 37 C.F.R. 1.98(a)(2).

Respectfully submitted,

KIE Y. AHN ET AL.

By their Representatives,

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Date June 7, 2005 By 
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Reg. No. 42,267

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: MS Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 7 day of June, 2005.

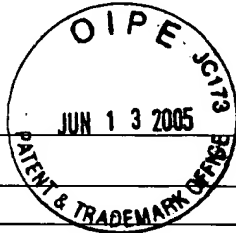
Name

KACIA LEE

Signature

Kacia Lee

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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
(Use as many sheets as necessary)



Complete if Known

Application Number	09/945,535
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First Named Inventor	Ahn, Kie
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Examiner Name	Blum, David

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Attorney Docket No: 1303.026US1

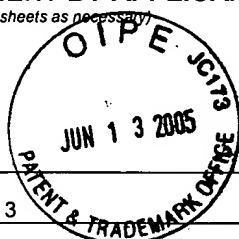
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EXAMINER

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Group Art Unit	2813
Examiner Name	Blum, David

Sheet 2 of 3

Attorney Docket No: 1303.026US1

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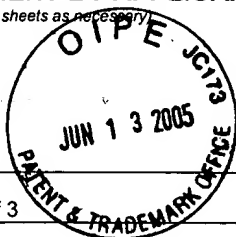
Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	T ²
	WO-04079796A3	09/16/2004	Ahn, K. Y., et al.	

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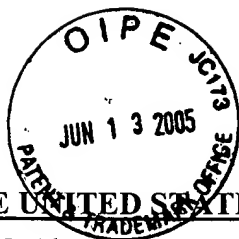
Attorney Docket No: 1303.026US1

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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Applicant: Kie Y. Ahn et al.

Examiner: David S. Blum

Serial No.: 09/945,535

Group Art Unit: 2813

Filed: August 30, 2001

Docket: 1303.026US1

Title: HIGHLY RELIABLE AMORPHOUS HIGH-K GATE OXIDE ZRO2

COMMUNICATION CONCERNING RELATED APPLICATION(S)

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Applicants would like to bring to the Examiner's attention the following related application(s) in the above-identified patent application:

<u>Serial/Patent No.</u>	<u>Filing Date</u>	<u>Attorney Docket</u>	<u>Title</u>
10/909959	August 2, 2004	1303.114US1	ATOMIC LAYER DEPOSITION OF ZIRCONIUM-DOPED TANTALUM OXIDE FILMS
10/931533	August 31, 2004	1303.119US1	ATOMIC LAYER DEPOSITED TITANIUM ALUMINUM OXIDE FILMS
10/926812	August 26, 2004	1303.121US1	RUTHENIUM GATE FOR A LANTHANIDE OXIDE DIELECTRIC LAYER
10/930167	August 31, 2004	1303.122US1	ATOMIC LAYER DEPOSITED LANTHANUM ALUMINUM OXIDE DIELECTRIC LAYER
11/010529	December 13, 2004	1303.126US1	ATOMIC LAYER DEPOSITED LANTHANUM HAFNIUM OXIDE DIELECTRICS
11/029757	January 5, 2005	1303.127US1	ATOMIC LAYER DEPOSITED HAFNIUM TANTALUM OXIDE DIELECTRICS
11/010766	December 13, 2004	1303.129US1	HYBRID ALD-CVD OF PrXOY/ZrO2 FILMS AS GATE DIELECTRICS
11/058563	February 15, 2005	1303.133US1	ATOMIC LAYER DEPOSITION OF Zr3N4/ZrO2 FILMS AS GATE DIELECTRICS

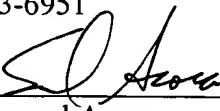
11/063717	February 23, 2005	1303.134US1	ATOMIC LAYER DEPOSITION OF Hf3N4/HfO2 FILMS AS GATE DIELECTRICS
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11/092072	March 29, 2005	1303.135US1	ALD OF AMORPHOUS LANTHANIDE DOPED TIOX FILMS
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11/084968	March 21, 2005	1303.083US2	Zr-Sn-Ti-O FILMS

Continuations and divisionals may be later filed on the cases listed above, or cited to the Examiner in any previous Communication Concerning Related Applications. Applicant requests that the Examiner review all continuations and divisionals of the above-listed or previously-cited patent applications before allowing the claims of the present patent application.

Respectfully submitted,
KIE Y. AHN ET AL.

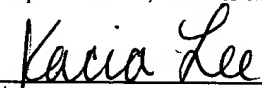
By Applicants' Representatives,
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By 
Suneel Arora
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CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Mail Stop Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 7 day of June, 2005.

Name KACIA LEE


Signature